

INCHANGE SEMICONDUCTOR

iscN-Channel MOSFET Transistor

TK12A53D, ITK12A53D

• FEATURES

- Low drain-source on-resistance: R_Ds(ON) = 0.5Ω (typ.)
- · Enhancement mode:

Vth = 2.0 to 4.0V (VDs = 10 V, ID=1.0mA)

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

Switching Voltage Regulators

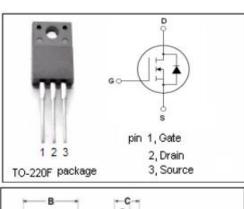
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

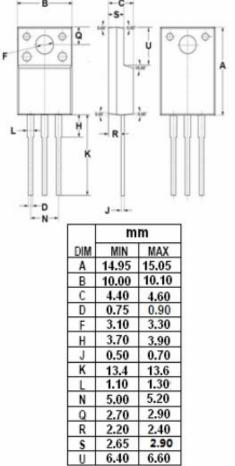
SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	525	V				
V _{GS}	Gate-Source Voltage	±30	V				
ID	Drain Current-Continuous	12	A				
I _{DM}	Drain Current-Single Pulsed	48	А				
PD	Total Dissipation @T _c =25°C	45	W				
Tj	Max. Operating Junction Temperature	150	°C				
T _{stg}	Storage Temperature	-55~150	°C				

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT		
Rth(ch-c)	Channel-to-case thermal resistance	2.78	°C /W		
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C /W		

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isc website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

 $T_{C}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	525			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = 10V; I _D =1.0mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =6A		500	580	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} =0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =525V; V _{GS} = 0V			10	μA
VSDF	Diode forward voltage	I _{DR} =12A, V _{GS} = 0 V			1.7	V

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